

## Features

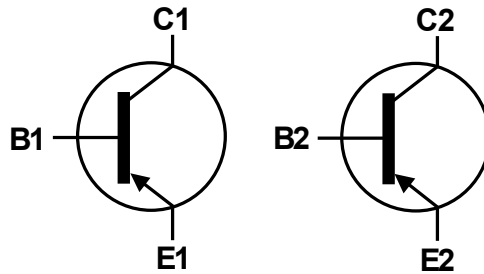
- $BV_{CEO} > -65V$
- $I_C = -100mA$  High Collector Current
- Complementary NPN Types Available (BC846AS)
- For Switching and AF Amplifier Applications
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony-Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.**  
<https://www.diodes.com/quality/product-definitions/>
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([BC856ASQ](#))**

## Mechanical Data

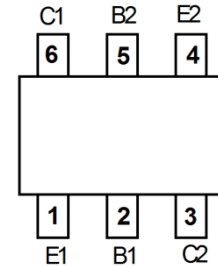
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound.  
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (Approximate)



Top View



Device Symbol



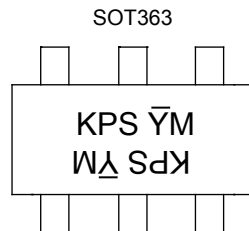
Top View Pin-Out

## Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
BC856AS-7	AEC-Q101	KPS	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



KPS = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: I = 2021)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	H	I	J	K	L	M	N	O	P	R	S	T
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Absolute Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-65	V
Emitter-Base Voltage	$V_{EBO}$	-5.0	V
Collector Current	$I_C$	-100	mA
Peak Collector Current	$I_{CM}$	-200	mA
Peak Emitter Current	$I_{EM}$	-200	mA
Power Dissipation (Note 5)	$P_D$	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-65 to +150	$^\circ\text{C}$

**Thermal Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_D$	200	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic (Note 6)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	-80	—	—	V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	-65	—	—	V	$I_C = -10\text{mA}$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-5	—	—	V	$I_E = -100\mu\text{A}$
DC Current Gain	$h_{FE}$	125	180	250	—	$V_{CE} = -5.0\text{V}, I_C = -2.0\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	-75 -250	-300 -650	mV	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$ $I_C = -100\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	-700 -850	—	mV	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$ $I_C = -100\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Voltage	$V_{BE(on)}$	-600	-650	-750 -820	mV	$V_{CE} = -5.0\text{V}, I_C = -2.0\text{mA}$ $V_{CE} = -5.0\text{V}, I_C = -10\text{mA}$
Collector-Cutoff Current	$I_{CES}$ $I_{CBO}$ $I_{CBO}$	— — —	— — —	-15 -15 -4.0	nA nA $\mu\text{A}$	$V_{CE} = -80\text{V}$ $V_{CB} = -30\text{V}$ $V_{CB} = -30\text{V}, T_A = +150^\circ\text{C}$
Gain Bandwidth Product	$f_T$	100	—	—	MHz	$V_{CE} = -5.0\text{V}, I_C = -10\text{mA}$ , $f = 100\text{MHz}$
Collector-Base Capacitance	$C_{CB}$	—	3	—	pF	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}$

- Notes:
- For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Short duration pulse test used to minimize self-heating effect.

**Typical Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

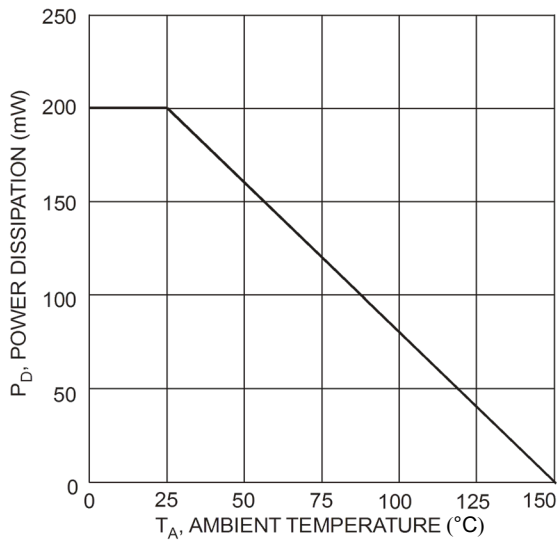


Fig. 1 Power Derating Curve

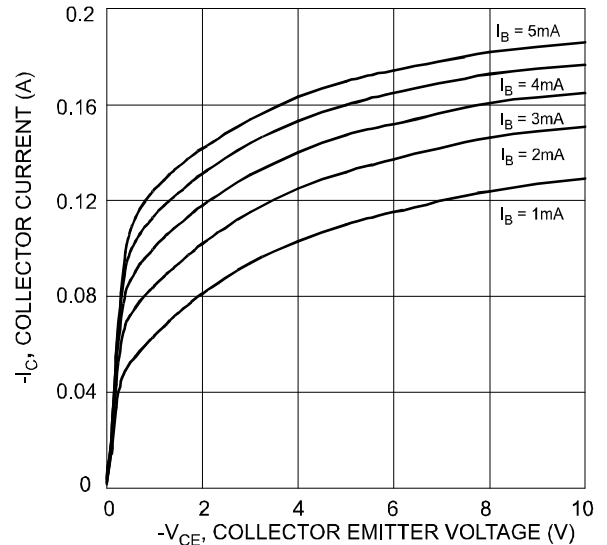


Fig. 2 Typical Collector Current vs. Collector Emitter Voltage

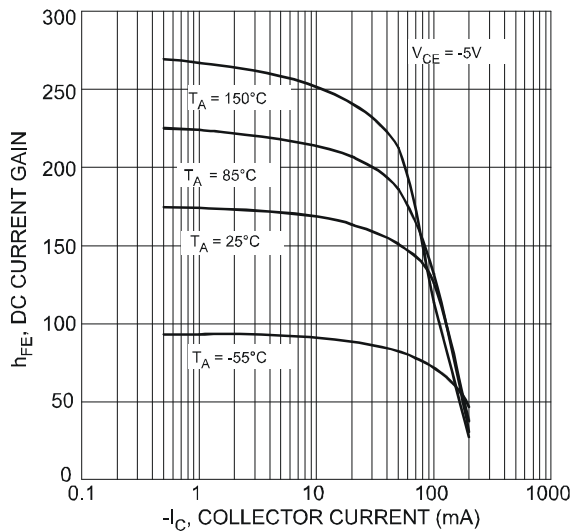


Fig. 3 Typical DC Current Gain vs. Collector Current

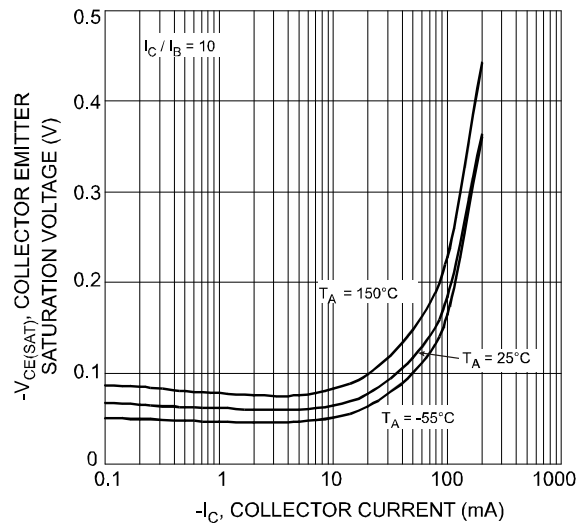


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

**Typical Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.) (continued)

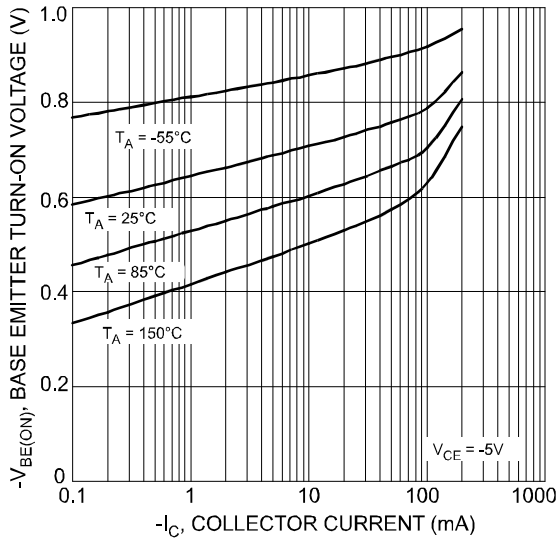


Fig. 5 Typical Base Emitter Turn-On Voltage vs. Collector Current

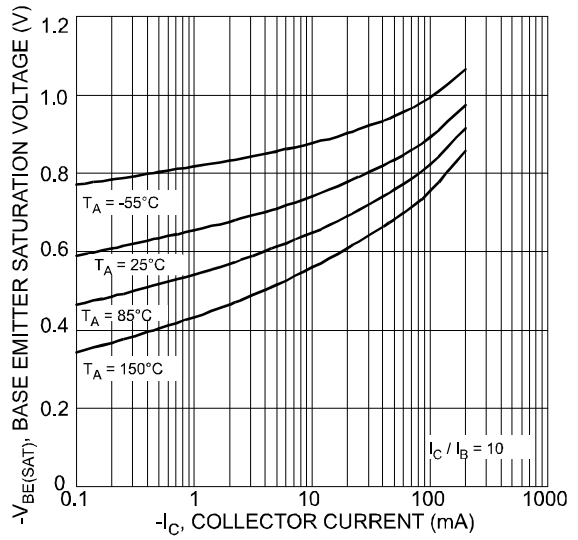


Fig. 6 Typical Base Emitter Saturation Voltage vs. Collector Current

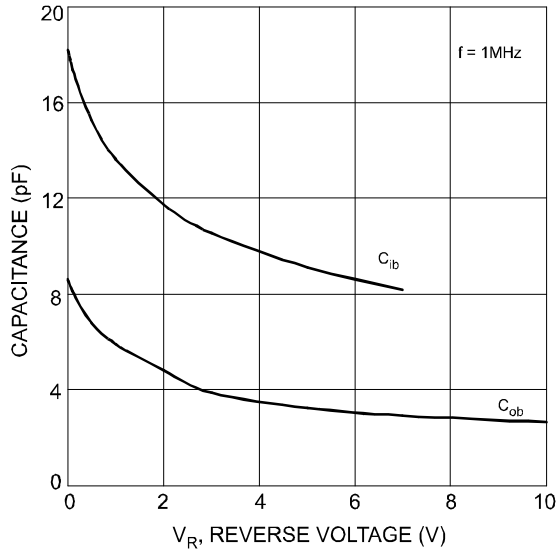


Fig. 7 Typical Capacitance Characteristics

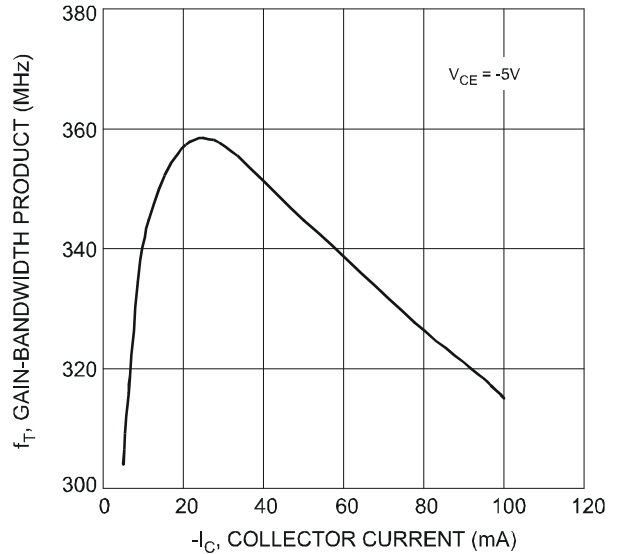
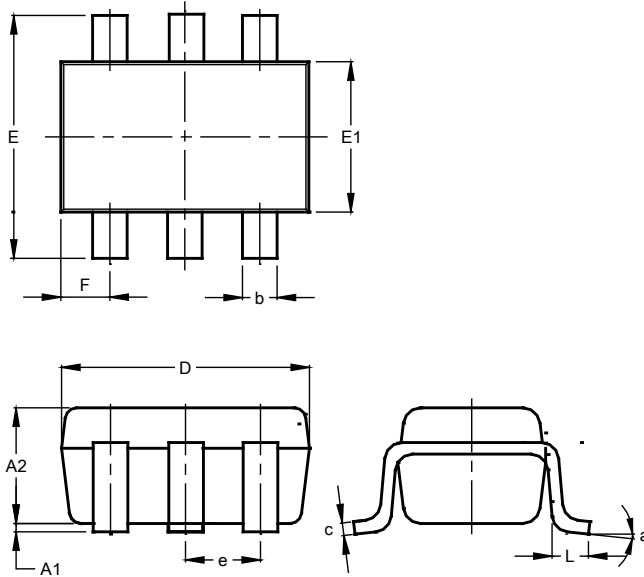


Fig. 8 Gain-Bandwidth Product vs. Collector Current

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT363

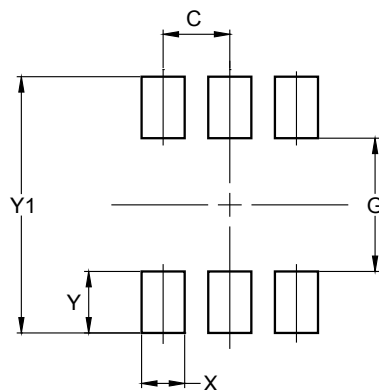


SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
<b>All Dimensions in mm</b>			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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